

0.8 A sensitive gate SCR

Datasheet — production data

Features

- $I_{T(RMS)} = 0.8\text{ A}$
- $V_{DRM}, V_{RRM} = 600\text{ V}$
- $I_{GT} = 30\text{ to }200\text{ }\mu\text{A}$

Applications

- Limited gate current topologies
- Ground fault circuit interrupters
- Overvoltage crowbar protection in power supplies
- Protection in electronic ballasts
- Capacitive discharge ignitions
- Ignitors (lighting, oven...)

Description

The X006 SCR can be used as on/off function in applications where topology does not offer high current for gate triggering.

This device is optimized in forward voltage drop and inrush current capabilities for reduced power losses and high reliability in harsh environments.

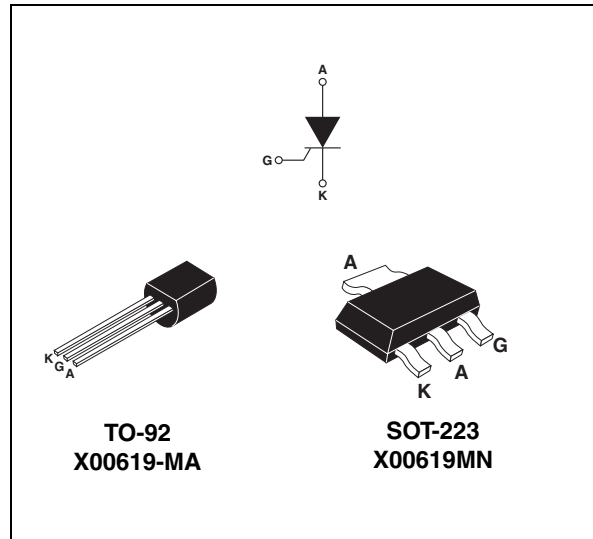


Table 1. Device summary

$I_{T(RMS)}$	0.8 A
V_{DRM} / V_{RRM}	600 V
I_{GT}	30 to 200 μA

1 Characteristics

Table 2. Absolute ratings (limiting values, $T_J = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	On-state rms current (180 °Conduction angle)	TO-92	$T_L = 83\text{ °C}$	0.8	A
		SOT-223	$T_c = 107\text{ °C}$		
$I_{T(AV)}$	Average on-state current (180 °Conduction angle)	TO-92	$T_L = 83\text{ °C}$	0.5	A
		SOT-223	$T_c = 107\text{ °C}$		
I_{TSM}	Non repetitive surge peak on-state current	$t_p = 8.3\text{ ms}$	$T_J = 25\text{ °C}$	10	A
		$t_p = 10\text{ ms}$		9	
I^2t	I^2t Value for fusing	$t_p = 10\text{ ms}$	$T_J = 25\text{ °C}$	0.4	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ ns}$	$F = 60\text{ Hz}$	$T_J = 125\text{ °C}$	50	$A/\mu s$
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu s$	$T_J = 125\text{ °C}$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125\text{ °C}$	0.1	W
T_{stg} T_J	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^{\circ}C$

Table 3. Electrical characteristics ($T_J = 25\text{ °C}$ unless otherwise specified)

Symbol	Test conditions			Value	Unit
I_{GT}	$V_D = 12\text{ V}$, $R_L = 140\text{ }\Omega$		MIN.	30	μA
			MAX.	200	
V_{GT}				0.8	V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$, $R_{GK} = 1\text{ k}\Omega$	$T_J = 125\text{ °C}$	MIN.	0.2	V
V_{RG}	$I_{RG} = 10\text{ }\mu A$		MIN.	5	V
I_H	$I_T = 50\text{ mA}$, $R_{GK} = 1\text{ k}\Omega$		MAX.	5	mA
I_L	$I_G = 1\text{ mA}$, $R_{GK} = 1\text{ k}\Omega$		MAX.	6	mA
dV/dt	$V_D = 67\% V_{DRM}$, $R_{GK} = 1\text{ k}\Omega$	$T_J = 125\text{ °C}$	MIN.	40	$V/\mu s$

Table 4. Static electrical characteristics

Symbol	Test conditions			Value	Unit
V _{TM}	I _{TM} = 1 A, t _p = 380 μs	T _j = 25 °C	MAX	1.35	V
V _{TO}	Threshold voltage	T _j = 125 °C		0.85	V
R _d	Dynamic resistance			245	mΩ
I _{DRM} I _{RRM}	V _{DRM} = V _{RRM} , R _{GK} = 1 kΩ	T _j = 25 °C		1	μA
		T _j = 125 °C		100	μA

Table 5. Thermal resistances

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction to leads (DC)	TO-92	Max.	$^{\circ}\text{C}/\text{W}$
$R_{th(j-c)}$	Junction to case (DC)	SOT-223		
$R_{th(j-a)}$	Junction to ambient (DC)	TO-92		
		SOT-223		
	$S = 5 \text{ cm}^2$			

Figure 1. Maximum average power dissipation versus average on-state current

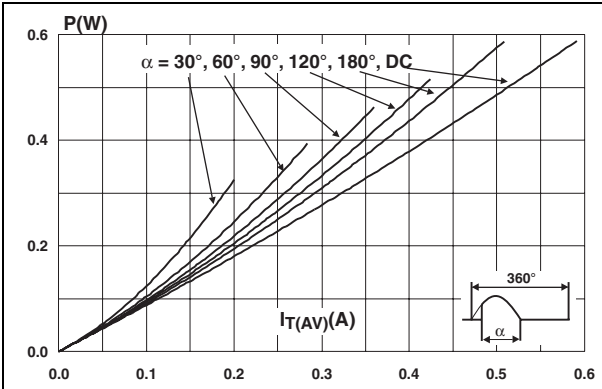


Figure 2. Average and DC on-state current versus case temperature (SOT-223)

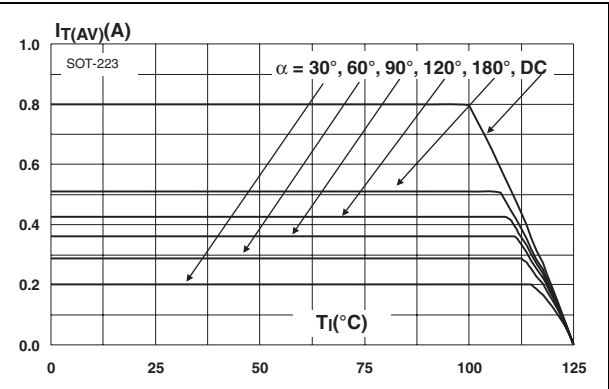


Figure 3. Average and DC on-state current versus lead temperature (TO-92)

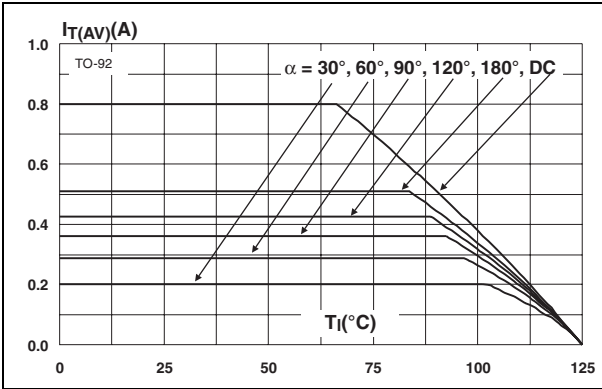


Figure 4. Average and DC on-state current versus ambient temperature (free air convection)

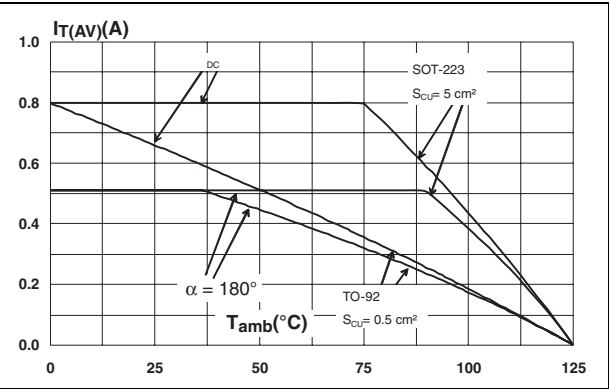


Figure 5. Relative variation of thermal impedance junction to ambient versus pulse duration

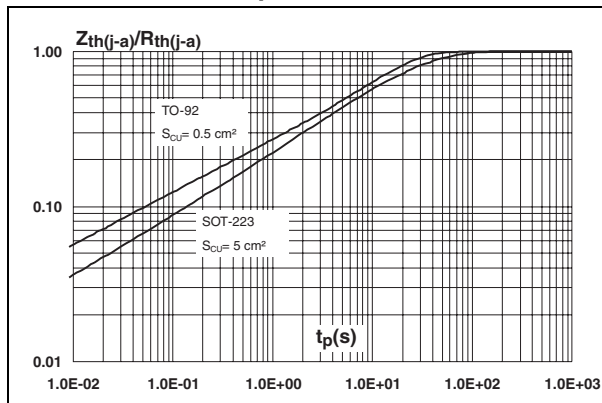


Figure 6. Relative variation of gate trigger, holding and latching current versus junction temperature

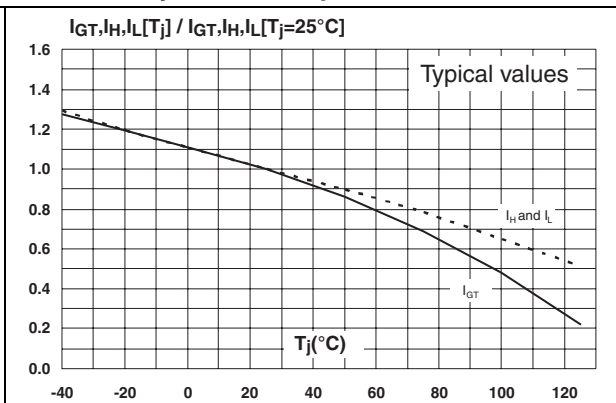


Figure 7. Relative variation of holding current versus gate-cathode resistance (typical values)

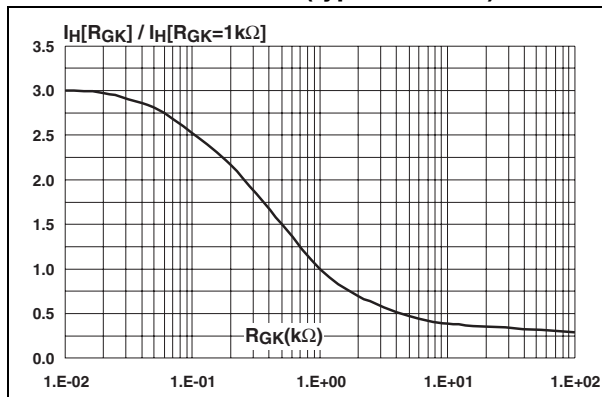


Figure 8. Relative variation of dV/dt immunity versus gate-cathode resistance (typical values)

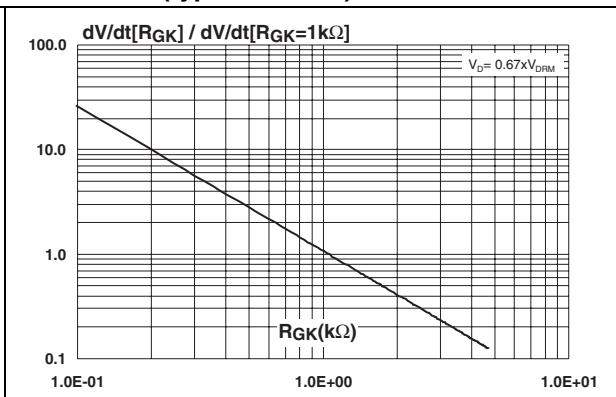


Figure 9. Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values)

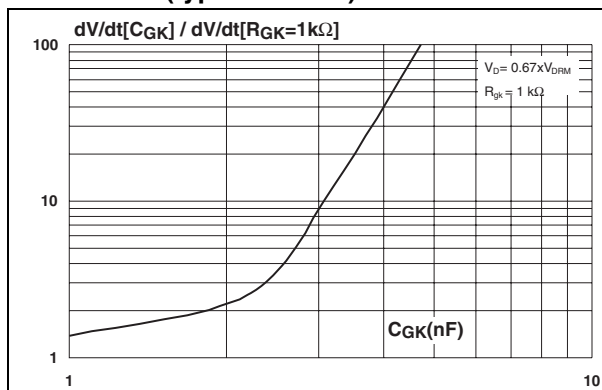


Figure 10. Surge peak on-state current versus number of cycles

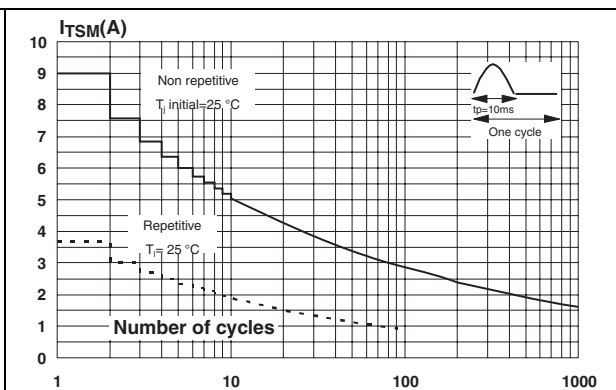


Figure 11. Non repetitive surge peak on state current for a sinusoidal pulse and corresponding value of I^2t

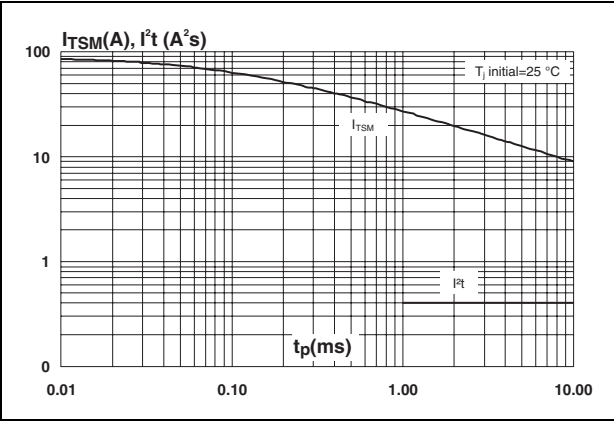


Figure 12. On-state characteristics (maximum values)

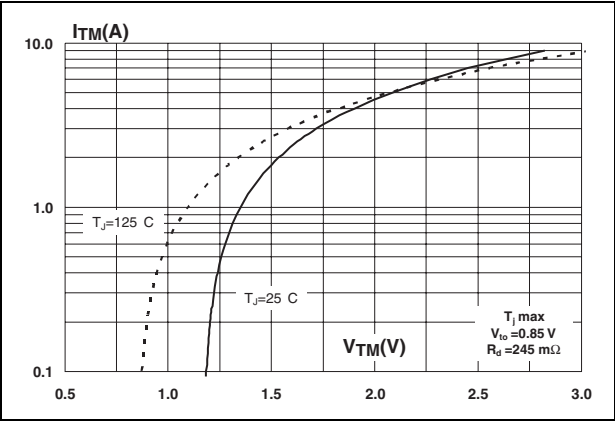
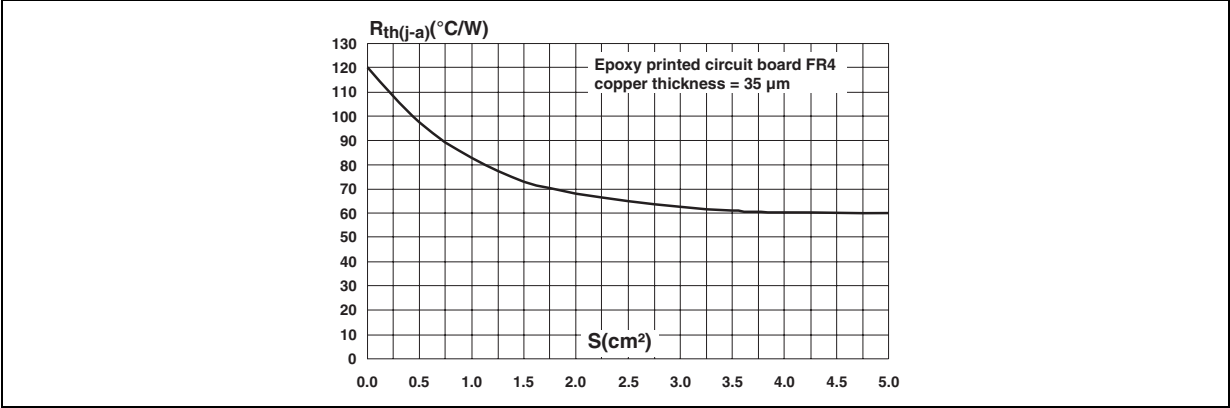
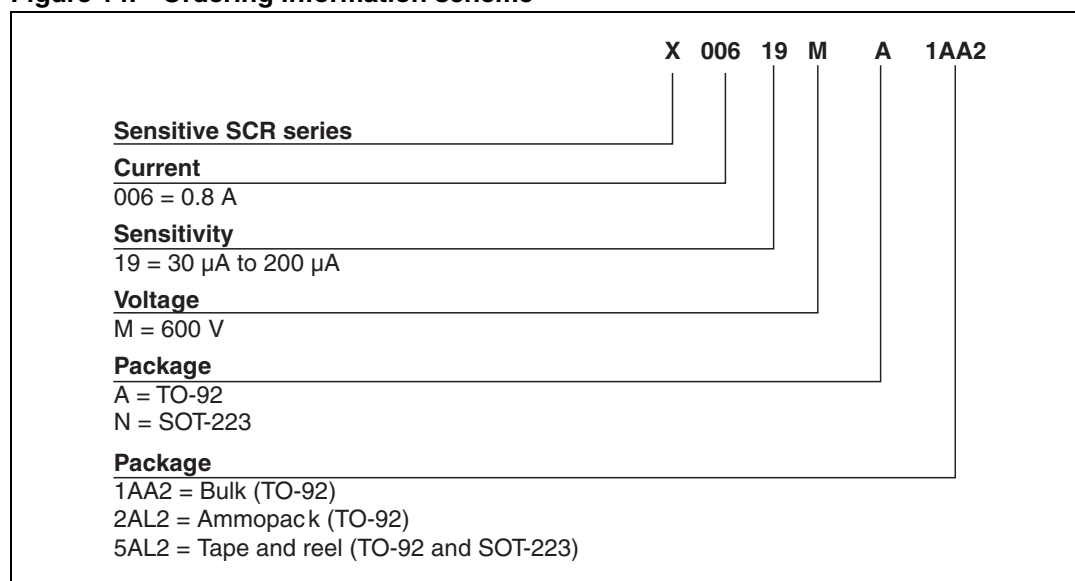


Figure 13. Thermal resistance junction to ambient versus copper surface under tab (SOT-223)



2 Ordering information scheme

Figure 14. Ordering information scheme



3 Package information

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 6. TO-92 (plastic) dimensions

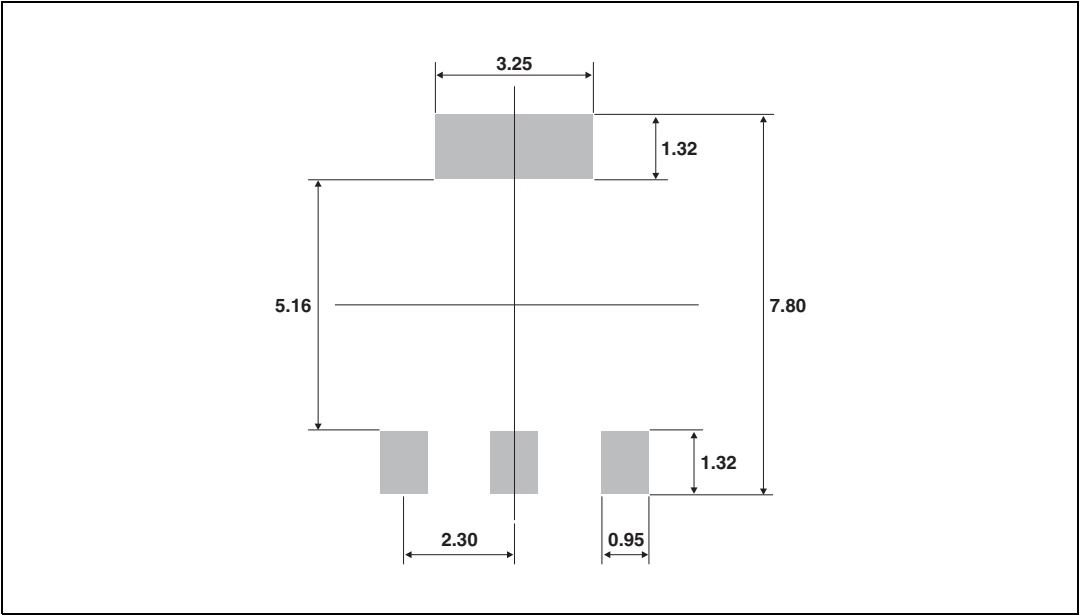
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	1.35	-	-	0.053	-
B	-	-	4.70	-	-	0.185
C	-	2.54	-	-	0.100	-
D	4.40	-	-	0.173	-	-
E	12.70	-	-	0.500	-	-
F	-	-	3.70	-	-	0.146
a	-	-	0.50	-	-	0.019

Table 7. SOT-223 dimensions

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.80			0.071
A1		0.02	0.10		0.001	0.004
B	0.60	0.70	0.85	0.024	0.027	0.033
B1	2.90	3.00	3.15	0.114	0.118	0.124
c	0.24	0.26	0.35	0.009	0.010	0.014
D ⁽¹⁾	6.30	6.50	6.70	0.248	0.256	0.264
e		2.3			0.090	
e1		4.6			0.181	
E ⁽¹⁾	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V	10° max					

1. Do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm (0.006inches)

Figure 15. SOT-223 footprint



4 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
X00619MA1AA2	X0619 MA	TO-92	0.2 g	2500	Bulk
X00619MA2AL2				2000	Ammopack
X00619MA5AL2				2000	Tape and reel
X00619MN5AL2	X0 619 MN	SOT-223	0.12 g	1000	

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
26-May-2009	1	First issue
03-May-2012	2	Added SOT-223 package.

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